



**PATENT APPLICATION**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of

Docket No: Q68148

Kuniaki YAGI, et al.

Appln. No.: 10/050,570

Group Art Unit: 1765

Confirmation No.: 7078

Examiner: SONG, MATTHEW

Filed: January 18, 2002

For: SINGLE CRYSTAL SIC AND METHOD OF PRODUCING THE SAME AS WELL  
AS SIC SEMICONDUCTOR DEVICE AND SIC COMPOSITE MATERIAL

**RECEIVED**  
**SEP 30 2003**  
**TC 1700**

**INFORMATION DISCLOSURE STATEMENT  
UNDER 37 C.F.R. §§ 1.97 and 1.98**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant hereby notifies the U.S. Patent and Trademark Office of the documents which are listed on the attached PTO/SB/08 A & B (modified) form and/or listed herein and which the Examiner may deem material to patentability of the claims of the above-identified application.

One copy of each of the listed documents is submitted herewith, along with a copy of the corresponding Communication from a Foreign Patent Office.

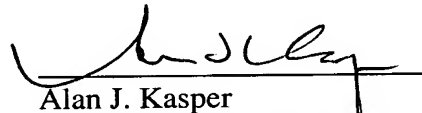
The present Information Disclosure Statement is being filed after the later of three months from the application's filing date and the mailing date of the first Office Action on the merits, but before a Final Office Action, Notice of Allowance, or an action that otherwise closes prosecution in the application (whichever is earlier), and therefore Applicant is filing concurrently herewith a Statement Under 37 C.F.R. § 1.97(e). No fee under 37 C.F.R. § 1.17(p) is required.

INFORMATION DISCLOSURE STATEMENT  
U.S. Appln. No.: 10/050,570  
Attorney Docket No. Q68148

The submission of the listed documents is not intended as an admission that any such document constitutes prior art against the claims of the present application. Applicant does not waive any right to take any action that would be appropriate to antedate or otherwise remove any listed document as a competent reference against the claims of the present application.

The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account. A duplicate copy of this paper is attached.

Respectfully submitted,

  
Alan J. Kasper  
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WASHINGTON OFFICE

**23373**

CUSTOMER NUMBER

Date: September 25, 2003



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STATEMENT UNDER 37 C.F.R. § 1.97(e)

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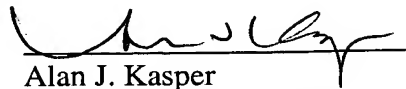
Sir:

The undersigned hereby states, upon information and belief:

That each item of information contained in the Information Disclosure Statement filed concurrently herewith was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of said Information Disclosure Statement.

Respectfully submitted,

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Date: September 25, 2003

Substitute for Form 1449 A &amp; B/PTO

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet

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of

1

## Complete if Known

Application Number	10/050,570
Confirmation Number	7078
Filing Date	January 18, 2002
First Named Inventor	Kuniaki YAGI
Art Unit	1765
Examiner Name	SONG, MATTHEW
Attorney Docket Number	Q68148

## U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code <sup>2</sup> (if known)		
		US 5,225,032	A	07-06-1993	Golecki
		US			
		US			
		US			
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		US			
		US			
		US			
		US			
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## FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation <sup>6</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)			
		EP	1 179 620	A1	02-13-2002	Nagasawa	
		EP	1 160 361	A1	12-05-2001	Nagasawa et al.	
		EP	0 632 145	A2	01-04-1995	Loboda	
		EP	0 639 661	A2	02-22-1995	Loboda et al.	

## NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation <sup>6</sup>
		BJÖRKETUN, L.-O. et al., "Interfacial Void Formation During Vapor Phase Growth of 3C-SiC on Si(0 0 1) and Si(1 1 1) Substrates Characterization by Transmission Electron Microscopy," Journal of Crystal Growth, December 1997, pp. 379-388, Vol. 182, No. 3-4, North-Holland Publishing Co., Amsterdam, NL.	
		YAGI, K. et al., "3C-SiC Growth By Alternate Supply of SiH <sub>2</sub> Cl <sub>2</sub> and C <sub>2</sub> H <sub>2</sub> ," Journal of Crystal Growth, April 1997, pp. 653-657, Vol. 174, No. 1-4, North-Holland Publishing Co., Amsterdam, NL.	
		STECKL, A.J. et al., "Epitaxial Growth of β-SiC on Si by RTCVD with C <sub>3</sub> H <sub>8</sub> and SiH <sub>4</sub> ," IEEE Transactions on Electron Devices, January 1992, pp. 64-74, Vol. 39, No. 1, IEEE Inc., New York, US.	

Examiner Signature

Date Considered

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>See Kind Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov), MPEP 901.04 or in the comment box of this document. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to indicate here if English language Translation is attached.